March 2004



AS7C513B

Features

- Industrial and commercial temperature
- Organization: 32,768 words × 16 bits
- Center power and ground pins
- High speed
- 10/12/15/20 ns address access time
- 5, 6, 7, 8 ns output enable access time
- Low power consumption: ACTIVE
- 605mW / max @ 10 ns
- Low power consumption: STANDBY
- 55 mW / max CMOS I/O

Logic block diagram

• 6T 0.18u CMOS Technology

- Easy memory expansion with \overline{CE} , \overline{OE} inputs
- TTL-compatible, three-state I/O
- 44-pin JEDEC standard package
- 400 mil SOJ
- 400 mil TSOP 2
- ESD protection \geq 2000 volts
- Latch-up current $\geq 200 \text{ mA}$

A0 V_{CC} A1 decoder A2 $32K \times 16$ GND A3 Array A4 Row A5 A6 Α7 I/O buffer I/O0–I/O7 Control circuit I/O8-I/O15 Column decoder WE UB-OE LB CE

Pin arrangement

44-Pin SOJ, TSOP 2 (400 mil)

NC A3 A2 A1 <u>A0</u> CE /O0 /O1 /O2 /O3 V _{CC} GND /O5 /O6 /O7 WE A14 A13 A12 A11	$ \begin{array}{c} 1 \\ 2 \\ 3 \\ 4 \\ 5 \\ 6 \\ 7 \\ 8 \\ 9 \\ 10 \\ 11 \\ 12 \\ 13 \\ 14 \\ 15 \\ 16 \\ 17 \\ 18 \\ 19 \\ 20 \\ 21 \\ \end{array} $	AS7C513B	44 43 42 41 40 39 38 37 36 35 34 33 32 31 30 29 28 27 26 25 25 24		A4 A5 A6 UB B B I/O15 I/O14 I/O12 GND V _{CC} I/O11 I/O10 I/O9 I/O8 NC A7 A8 A9 A10	
				H		
NC	22		23		NC	

Selection guide					n
	-10	-12	-15	-20	Unit
Maximum address access time	10	12	15	20	ns
Maximum output enable access time	5	6	7	8	ns
Maximum operating current	110	100	90	80	mA
Maximum CMOS standby current	10	10	10	C 10	mA
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26/04, v.1.3	Alliance Semice	onductor	Nº.	P. 1 of 9)

3/26/04, v.1.3

Functional description

The AS7C513B is a high performance CMOS 524,288-bit Static Random Access Memory (SRAM) device organized as 32,768 words $\times 16$ bits. They are designed for memory applications where fast data access, low power, and simple interfacing are desired.

Equal address access and cycle times (t_{AA}, t_{RC}, t_{WC}) of 10/12/15/20 ns with output enable access times (t_{OE}) of 5, 6, 7, 8 ns are ideal for high performance applications. The chip enable input \overline{CE} permits easy memory expansion with multiple-bank memory systems.

When \overline{CE} is high, the device enters standby mode. If inputs are still toggling, the device consumes I_{SB} power. If the bus is static, then the full standby power is reached (I_{SB1}). The AS7C513B is guaranteed not to exceed 55mW power consumption under nominal full standby conditions.

A write cycle is accomplished by asserting write enable (\overline{WE}), (\overline{UB}) and/or (\overline{LB}), and chip enable (\overline{CE}). Data on the input pins I/O0 - I/O7, and/or I/O8 – I/O15, is written on the rising edge of \overline{WE} (write cycle 1) or \overline{CE} (write cycle 2). To avoid bus contention, external devices should drive I/O pins only after outputs have been disabled with output enable (\overline{OE}) or write enable (\overline{WE}).

A read cycle is accomplished by asserting output enable (\overline{OE}) , (\overline{UB}) and (\overline{LB}) , and chip enable (\overline{CE}) , with write enable (\overline{WE}) high. The chips drive I/O pins with the data word referenced by the input address. When either chip enable or output enable is inactive, or write enable is active, or (\overline{UB}) and (\overline{LB}) , output drivers stay in high-impedance mode.

The devices provide multiple center power and ground pins, and separate byte enable controls, allowing individual bytes to be written and read. \overline{LB} controls the lower bits, I/O0 – I/O7, and \overline{UB} controls the higher bits, I/O8 – I/O15.

All chip inputs and outputs are TTL-compatible. The AS7C513B is packaged in common industry standard packages.

Absolute maximum ratings

Parameter	Symbol	Min	Max	Unit
Voltage on V _{CC} relative to GND	V _{t1}	-0.50	+7.0	V
Voltage on any pin relative to GND	V _{t2}	-0.50	V _{CC} +0.50	V
Power dissipation	P _D	-	1.0	W
Storage temperature (plastic)	T _{stg}	-65	+150	° C
Ambient temperature with V_{CC} applied	T _{bias}	-55	+125	° C
DC current into outputs (low)	I _{OUT}	_	20	mA

NOTE: Stresses greater than those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions outside those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Truth table

CE	WE	OE	LB	UB	I/O0–I/O7	I/O8–I/O15	Mode
Н	Х	Х	Х	Х	High Z	High Z	Standby (I_{SB}, I_{SBI})
L	Н	L	L	Н	D _{OUT}	High Z	Read I/O0–I/O7 (I _{CC})
L	Н	L	Н	L	High Z	D _{OUT}	Read I/O8–I/O15 (I _{CC})
L	Н	L	L	L	D _{OUT}	D _{OUT}	Read I/O0–I/O15 (I _{CC})
L	L	Х	L	L	D _{IN}	D _{IN}	Write I/O0–I/O15 (I _{CC})
L	L	Х	L	Н	D _{IN}	High Z	Write I/O0–I/O7 (I _{CC})
L	L	Х	Н	L	High Z	D _{IN}	Write I/O8–I/O15 (I _{CC})
L L	H X	H X	X H	X H	High Z	High Z	Output disable (I _{CC})

Key: X = Don't care; L = Low; H = High



Recommended operating conditions

Parameter	Parameter			Typical	Max	Unit
Supply voltage		V _{CC}	4.5	5	5.5	V
In part welte as		V _{IH}	2.2	-	V _{CC} + 0.5	
Input voltage		V _{IL}	-0.5	-	0.8	V
	commercial	T _A	0	-	70	° C
Ambient operating temperature	industrial	T _A	-40	-	85	° C

 V_{IL} min = -1.0V for pulse width less than 5ns

 V_{IH} max = V_{CC} +2.0V for pulse width less than 5ns.

DC operating characteristics (over the operating range) I

			-1	10	-1	2	-1	15	-2	:0	
Parameter	Sym	Test conditions	Min	Max	Min	Max	Min	Max	Min	Max	Unit
Input leakage current	$\mid I_{LI} \mid$	V _{CC} = Max V _{IN} = GND to V _{CC}	I	1	I	1	I	1	I	1	μA
Output leakage current	I _{LO}	$V_{CC} = Max$ $V_{OUT} = GND$ to V_{CC}	Ι	1	I	1		1	Ι	1	μA
Operating power supply current	I _{CC}	$V_{CC} = Max, \overline{CE} \le V_{IL}$ f = f _{Max} , I _{OUT} = 0mA	Ι	110	I	100	I	90		80	mA
Standby nowor	I _{SB}	$V_{CC} = Max, \overline{CE} \ge V_{IH}$ $f = f_{Max}$	Ι	50	I	45	I	45	I	40	mA
Standby power supply current	I _{SB1}	$\begin{split} V_{CC} &= Max, \ \overline{CE} \geq V_{CC} - 0.2V \\ V_{IN} \leq 0.2V \ or \\ V_{IN} \geq V_{CC} - 0.2V, \ f = 0 \end{split}$	_	10		10	Ι	10		10	mA
Output voltage	V _{OL}	I_{OL} = 8 mA, V_{CC} = Min	١	0.4	I	0.4	-	0.4	-	0.4	V
Output voltage	V _{OH}	I_{OH} = -4 mA, V_{CC} = Min	2.4	_	2.4	_	2.4	_	2.4	_	V

Capacitance (f = 1MHz, $T_a = 25^{\circ} C$, $V_{CC} = NOMINAL)^2$

Parameter	Symbol	Signals	Test conditions	Max	Unit
Input capacitance	C _{IN}	A, $\overline{\text{CE}}$, $\overline{\text{WE}}$, $\overline{\text{OE}}$, $\overline{\text{LB}}$, $\overline{\text{UB}}$	$V_{in} = 0V$	5	pF
I/O capacitance	C _{I/O}	I/O	$V_{in} = V_{out} = 0V$	7	pF

Read cycle (over the operating range) ^{3,9}

		-]	10	-]	12	-1	15	-2	20		
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Unit	Notes
Read cycle time	t _{RC}	10	_	12	I	15	_	20	I	ns	
Address access time	t _{AA}	-	10	-	12	-	15	-	20	ns	3
Chip enable (\overline{CE}) access time	t _{ACE}	_	10	_	12	_	15	_	20	ns	3
Output enable (\overline{OE}) access time	t _{OE}	_	5	_	6	_	7	_	8	ns	
Output hold from address change	t _{OH}	3	_	3	Ι	3	_	3	Ι	ns	5

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		-1	10	-]	12	-]	15	-2	20		
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Unit	Notes
$\overline{\text{CE}}$ low to output in low Z	t _{CLZ}	3	_	3	_	3	_	3	_	ns	4,5
$\overline{\text{CE}}$ high to output in high Z	t _{CHZ}	I	4	Ι	5	_	6	_	7	ns	4,5
\overline{OE} low to output in low Z	t _{OLZ}	0	-	0	-	0	-	0	-	ns	4,5
Byte select access time	t _{BA}	-	5	-	6	-	7	-	8	ns	
Byte select Low to low Z	t _{BLZ}	0	-	0	-	0	-	0	-	ns	4,5
Byte select High to high Z	t _{BHZ}	-	5	_	6	-	6	-	7	ns	4,5
OE high to output in high Z	t _{OHZ}	-	4	_	5	-	6	-	7	ns	4,5
Power up time	t _{PU}	0	_	0	_	0	_	0	_	ns	4,5
Power down time	t _{PD}	-	10	_	12	_	15		20	ns	4,5

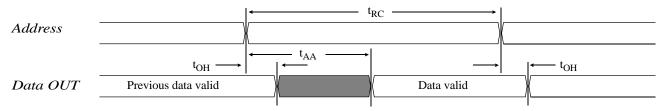
Key to switching waveforms

Rising input

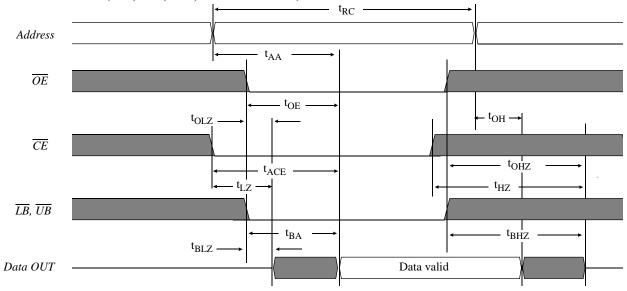
— Falling input

Undefined output/don't care

Read waveform 1 (address controlled)^{3,6,7,9}



Read waveform 2 (CE, OE, UB, LB controlled)^{3,6,8,9}

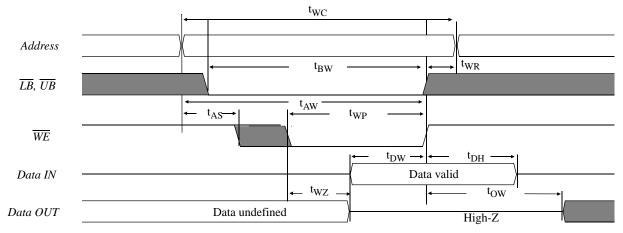




	<u> </u>	-]	10	-]	12	-1	15	-2	20		
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Unit	Notes
Write cycle time	t _{WC}	10	_	12	_	15	-	20	_	ns	
Chip enable (\overline{CE}) to write end	t _{CW}	8	_	9	_	10	_	12	_	ns	
Address setup to write end	t _{AW}	8	-	9	-	10	-	12	-	ns	
Address setup time	t _{AS}	0	-	0	-	0	-	0	-	ns	
Write pulse width	t _{WP}	7	-	8	-	9	-	12	-	ns	
Write recovery time	t _{WR}	0	-	0	-	0	-	0	-	ns	
Address hold from end of write	t _{AH}	0	-	0	-	0	-	0	-	ns	
Data valid to write end	t _{DW}	5	-	6	-	8	-	10	-	ns	
Data hold time	t _{DH}	0	-	0	-	0	-	0	-	ns	5
Write enable to output in high Z	t _{WZ}	_	5	_	6	_	7	_	8	ns	4,5
Output active from write end	t _{OW}	1	_	1	_	1	-	2	-	ns	4,5
Byte select low to end of write	t _{BW}	7	_	8	_	9	_	9	_	ns	

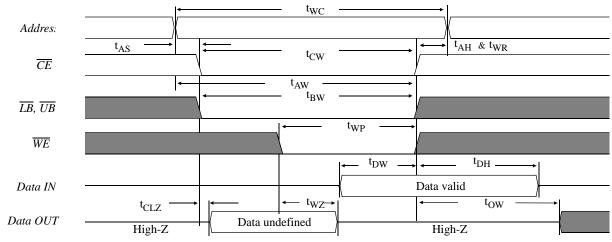
Write cycle (over the operating range)¹¹

Write waveform 1(WE controlled)¹¹



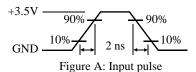


Write waveform 2 (CE controlled)¹¹



AC test conditions

- Output load: see Figure B.
- Input pulse level: GND to 3.5V. See Figure A.
- Input rise and fall times: 2 ns. See Figure A.
- Input and output timing reference levels: 1.5V.



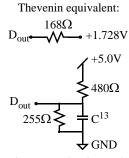
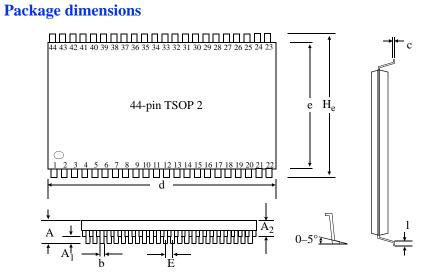


Figure B: 5.0V Output load

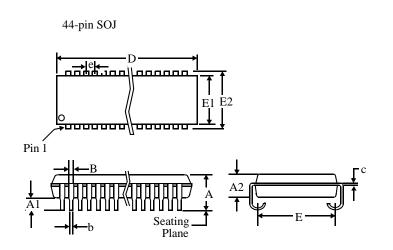
Notes

- 1 During V_{CC} power-up, a pull-up resistor to V_{CC} on \overline{CE} is required to meet I_{SB} specification.
- 2 This parameter is sampled, but not 100% tested.
- 3 For test conditions, see *AC Test Conditions*, Figures A and B.
- 4 These parameters are specified with $C_L = 5pF$, as in Figure B. Transition is measured $\pm 500mV$ from steady-state voltage.
- 5 This parameter is guaranteed, but not 100% tested.
- $\overline{\text{WE}}$ is High for read cycle.
- 7 $\overline{\text{CE}}$ and $\overline{\text{OE}}$ are Low for read cycle.
- 8 Address valid prior to or coincident with $\overline{\text{CE}}$ transition Low.
- 9 All read cycle timings are referenced from the last valid address to the first transitioning address.
- 10 Not applicable.
- 11 All write cycle timings are referenced from the last valid address to the first transitioning address.
- 12 Not applicable.
- 13 C=30pF, except on High Z and Low Z parameters, where C=5pF.

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	44-pin 7	TSOP 2			
Symbol	Min (mm)	Max (mm)			
А		1.2			
A ₁	0.05	0.15			
A ₂	0.95	1.05			
b	0.3	0.45			
с	0.12	0.21			
d	18.31	18.52			
e	10.06	10.26			
H _e	11.68	11.94			
Е	0.80 (typical)				
1	0.40	0.60			



	44-pin SOJ 400 mil							
Symbol	Min	Max						
А	0.128	0.148						
A1	0.025	-						
A2	0.105	0.115						
В	0.026	0.032						
b	0.015	0.020						
с	0.007	0.013						
D	1.120	1.130						
Е	0.370	NOM						
E1	0.395	0.405						
E2	0.435 0.445							
e	0.050	NOM						



Ordering codes

Package\Access time		10 ns	12 ns	15 ns	20 ns
Plastic SOJ, 400 mil	Commercial	AS7C513B-10JC	AS7C513B-12JC	AS7C513B-15JC	AS7C513B-20JC
	Industrial	AS7C513B-10JI	AS7C513B-12JI	AS7C513B-15JI	AS7C513B-20JI
TSOP 2, 18.4×10.2 mm	Commercial	AS7C513B-10TC	AS7C513B-12TC	AS7C513B-15TC	AS7C513B-20TC
	Industrial	AS7C513B-10TI	AS7C513B-12TI	AS7C513B-15TI	AS7C513B-20TI

Part numbering system

AS7C	513B	-XX	X	С
SRAM prefix	Device number	Access time	Package: J = SOJ 400 mil T =TSOP 2 18.4×10.2 mm	Temperature range: C = Commercial, 0°C to 70°C I = Industrial, -40°C to 85°C



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